

SILICON MIXER DIODE

DESCRIPTION:

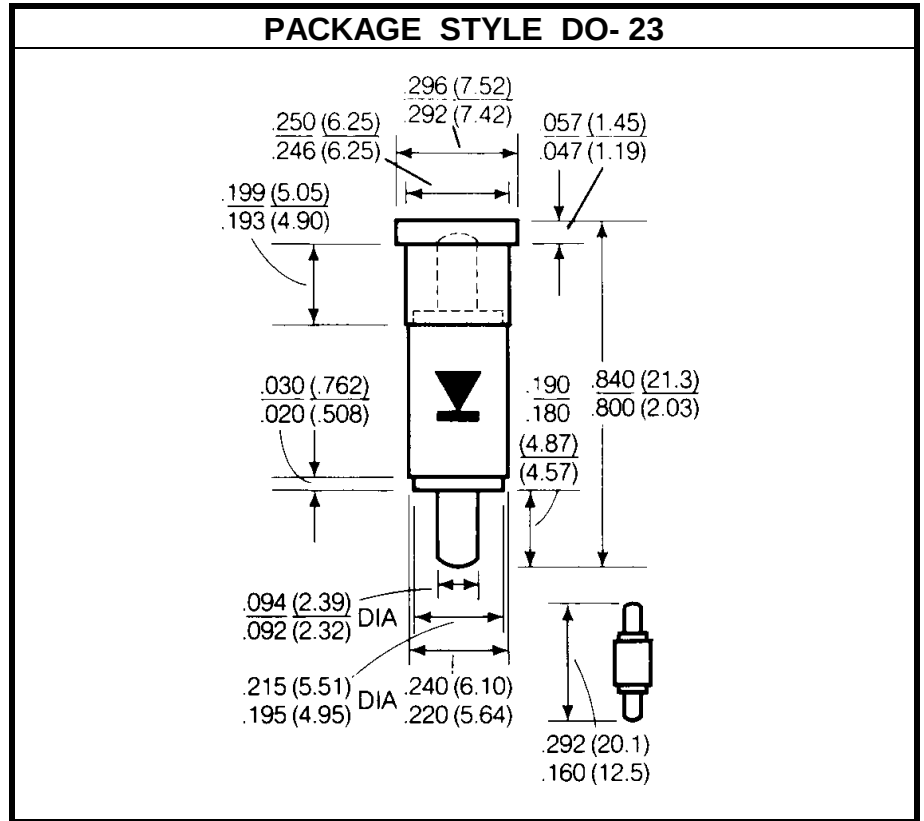
The **ASI 1N415E** is a Silicon Mixer Diode Designed for Applications Operating From 8.0 to 12.4 GHz.

FEATURES:

- High burnout resistance
- Low noise figure
- Hermetically sealed package

MAXIMUM RATINGS

I_F	20 mA
V_R	1.0 V
P_{DISS}	2.0 (ERGS) @ $T_C = 25^\circ\text{C}$
T_J	-55°C to $+150^\circ\text{C}$
T_{STG}	-55°C to $+150^\circ\text{C}$



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIM	UNITS
N_F	$F = 9375\text{ MHz}$ $R_L = 100\ \Omega$ $P_{I0} = 1.0\text{ mW}$ $I_F = 30\text{ MHz}$ $N_{Fif} = 1.5\text{ dB}$			7.5	dB
V_{SWR}				1.3	
Z_{IF}	$R_L = 22\ \Omega$ $f = 1000\text{ Hz}$	335		465	Ω
frange		8.0		12.4	GHz